

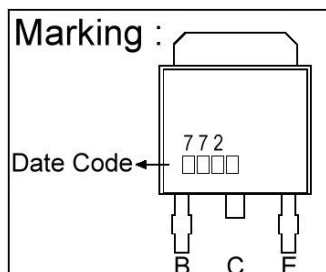
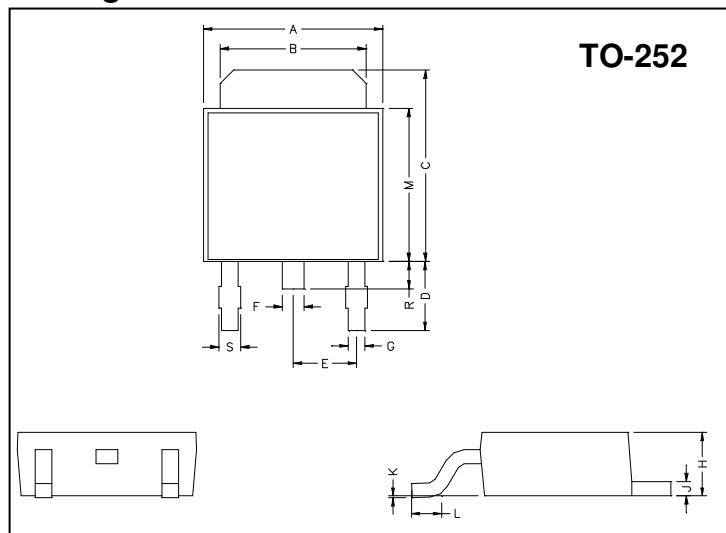
## GJ772

### PNP EPITAXIAL PLANAR TRANSISTOR

#### Description

The GJ772 is designed for using in output stage of 10W amplifier, voltage regulator, DC-DC converter and relay driver.

#### Package Dimensions



| REF. | Millimeter |      | REF. | Millimeter |      |
|------|------------|------|------|------------|------|
|      | Min.       | Max. |      | Min.       | Max. |
| A    | 6.40       | 6.80 | G    | 0.50       | 0.70 |
| B    | 5.20       | 5.50 | H    | 2.20       | 2.40 |
| C    | 6.80       | 7.20 | J    | 0.45       | 0.55 |
| D    | 2.40       | 3.00 | K    | 0          | 0.15 |
| E    | 2.30 REF.  |      | L    | 0.90       | 1.50 |
| F    | 0.70       | 0.90 | M    | 5.40       | 5.80 |
| S    | 0.60       | 0.90 | R    | 0.80       | 1.20 |

#### Absolute Maximum Ratings at Ta = 25°C

| Parameter                        | Symbol | Ratings  | Unit |
|----------------------------------|--------|----------|------|
| Junction Temperature             | Tj     | +150     | °C   |
| Storage Temperature              | Tstg   | -55~+150 | °C   |
| Collector to Base Voltage        | Vcbo   | -40      | V    |
| Collector to Emitter Voltage     | Vceo   | -30      | V    |
| Emitter to Base Voltage          | Vebo   | -5       | V    |
| Collector Current                | Ic     | -3       | A    |
| Collector Current (Pulse)        | Ic     | -7       | A    |
| Base Current                     | Ib     | -0.6     | A    |
| Total Power Dissipation(Tc=25°C) | Pd     | 10       | W    |

#### Electrical Characteristics (Ta = 25°C)

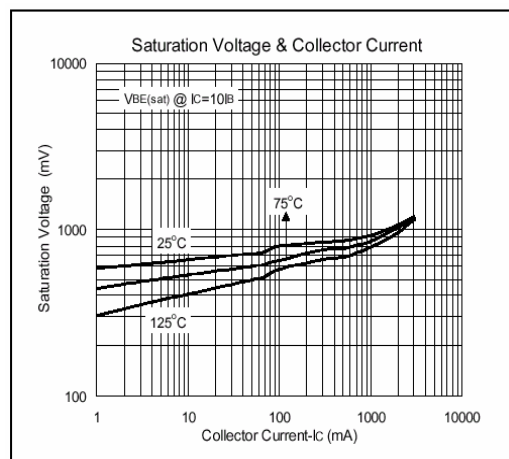
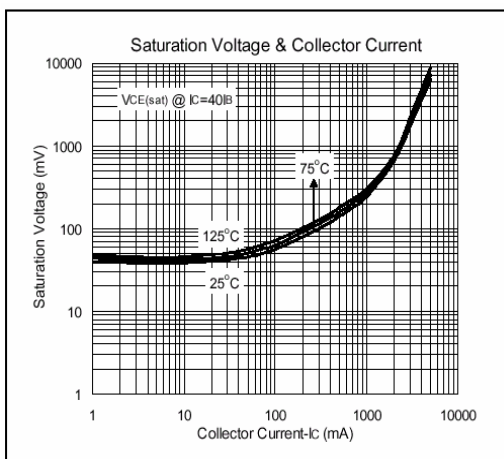
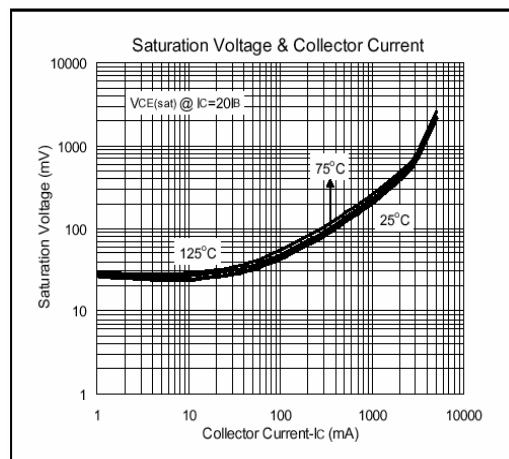
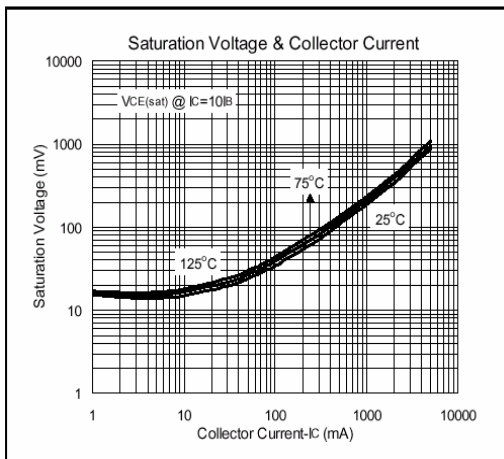
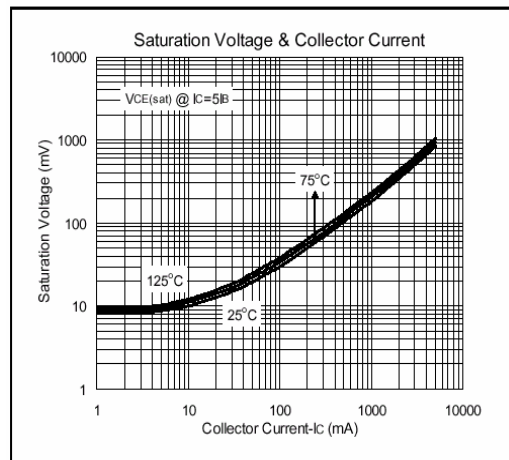
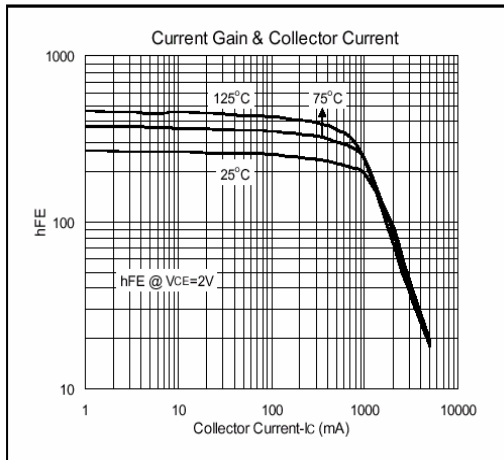
| Symbol    | Min. | Typ. | Max. | Unit | Test Conditions             |
|-----------|------|------|------|------|-----------------------------|
| BVcbo     | -40  | -    | -    | V    | Ic=-100uA, IE=0             |
| BVceo     | -30  | -    | -    | V    | Ic=-1mA, Ib=0               |
| BVebo     | -5   | -    | -    | V    | IE=-10uA, Ic=0              |
| Icbo      | -    | -    | -1   | uA   | Vcb=-30V, IE=0              |
| IEBO      | -    | -    | -1   | uA   | VEB=-3V, Ic=0               |
| *VCE(sat) | -    | -0.3 | -0.5 | V    | Ic=-2A, Ib=-0.2A            |
| *VBE(sat) | -    | -1   | -2   | V    | Ic=-2A, Ib=-0.2A            |
| *hFE1     | 30   | -    | -    |      | VCE=-2V, Ic=-20mA           |
| *hFE2     | 100  | -    | 500  |      | VCE=-2V, Ic=-1A             |
| fT        | -    | 80   | -    | MHz  | VCE=-5V, Ic=-0.1A, f=100MHz |
| Cob       | -    | 55   | -    | pF   | Vcb=-10V, IE=0, f=1MHz      |

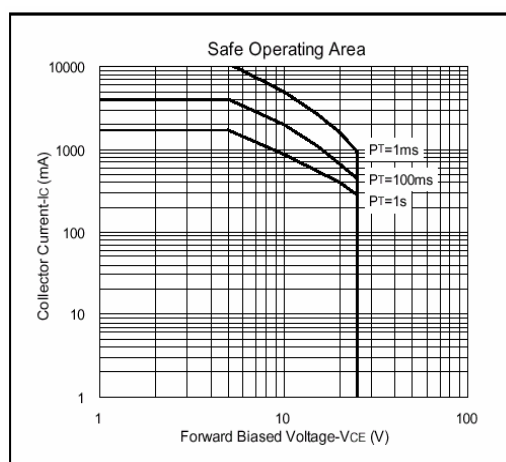
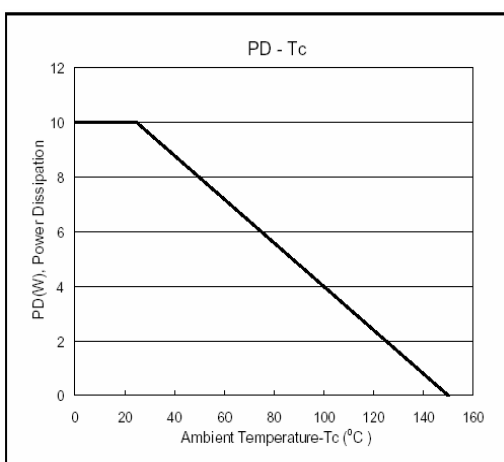
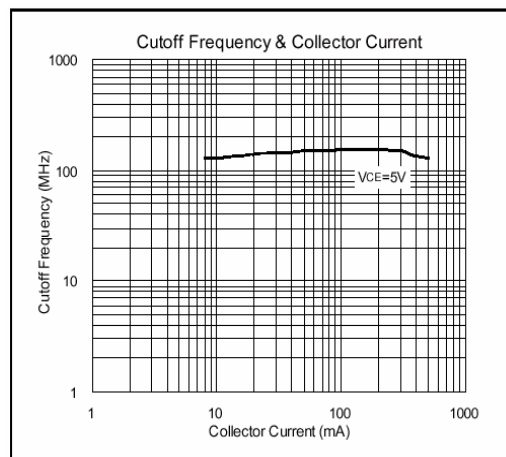
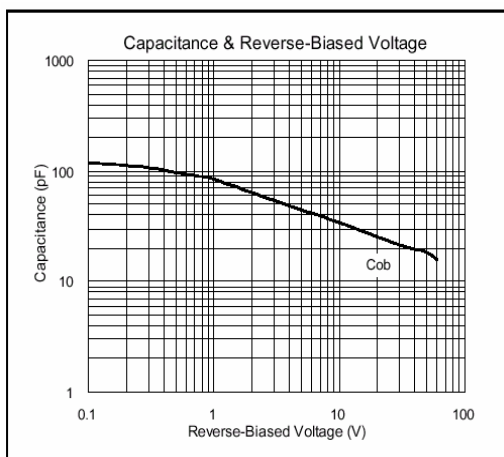
\* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

#### Classification Of hFE2

| Rank  | Q         | P         | E         |
|-------|-----------|-----------|-----------|
| Range | 100 - 200 | 160 - 320 | 250 - 500 |

## Characteristics Curve





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